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Ami

At this time, the first adhesive layer 16 is formed so as to be narrower than the wiring board 2 in width to avoid an extended-out portion thereof. However, a recessed portion 17 of an adhesive occurs due to such formation.--

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Page 19, please replace the second paragraph bridging lines 18-22 with the following replacement paragraph:

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A6

--Since the encapsulation is done after the bonding using the metal thin wires 4 in the fifth embodiment, the pads won't become dirty and a bad influence on wire bonding can be avoided, thus making it possible to improve the reliability of connections of the wiring portions.--

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**IN THE CLAIMS:**

Please amend the claims as follows:

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- Sub B.1
- A7
1. (Amended) A semiconductor device, comprising:
- a semiconductor chip;
  - metal thin wires respectively connected to electrodes on said semiconductor chip;
  - a wiring board having an opening for accommodating said semiconductor chip and being electrically connected to said semiconductor chip by said metal thin wires;
  - a heat spreader having said semiconductor chip and said wiring board provided thereon;
  - an adhesive layer which is provided over a principle surface of said heat spreader and bonds said semiconductor chip and said wiring board to each other;

AMENDMENT

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and

an encapsulating resin for sealing at least said metal thin wires,

wherein said semiconductor chip is disposed in the opening of said wiring board, and is separated from edges of said wiring board that collectively define the opening by a space so that said semiconductor chip does not completely cover said heat spreader within the opening, and

wherein a portion of said heat spreader within the opening that is not covered by said semiconductor chip being completely covered by said adhesive layer.

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Amend

2. (Amended) The semiconductor device as claimed in claim 1, further comprising a second adhesive layer having the same thermal characteristic as said adhesive layer provided over the reverse surface of said heat spreader.

3. (Amended) The semiconductor device as claimed in claim 2, further comprising a radiating fin provided over said second adhesive layer.

Sub  
B2

4. (Amended) A method of manufacturing a semiconductor device, comprising the following steps:

preparing a heat spreader;

forming an adhesive layer over a principal surface of said heat spreader;

disposing a semiconductor chip and a wiring board over said adhesive layer, the wiring board having an opening for accommodating said semiconductor chip, said

semiconductor chip being disposed in the opening of said wiring board, and being separated from edges of said wiring board that collectively define the opening by a space so that said semiconductor chip does not completely cover said heat spreader within the opening, a portion of said heat spreader within the opening that is not covered by said semiconductor chip being completely covered by said adhesive layer;

connecting electrodes of said semiconductor chip and said wiring board by metal thin wires; and

sealing at least said metal thin wires with an encapsulating resin.

5. (Amended) A method of manufacturing a semiconductor device, comprising the following steps:

preparing a heat spreader;

forming a first adhesive layer and a second adhesive layer over a principal surface of said heat spreader;

forming a wiring board over said first adhesive layer;

forming a semiconductor chip over said second adhesive layer;

connecting electrodes of said semiconductor chip and said wiring board by metal thin wires;

sealing said second adhesive layer and part of said semiconductor chip with a first encapsulating resin; and

sealing said metal thin wires and said semiconductor chip with a second encapsulating resin after said first encapsulating resin has been cured.

Sub B3  
7. (Amended) A method a manufacturing a semiconductor device, comprising the following steps:

preparing a heat spreader;

forming a first adhesive layer and a second adhesive layer over a principal surface of said heat spreader;

forming a wiring board over said first adhesive layer;

forming a semiconductor chip over said second adhesive layer;

connecting electrodes of said semiconductor chip and said wiring board by metal thin wires;

sealing said second adhesive layer and part of said semiconductor chip with an encapsulating resin; and

after said encapsulating resin has at least partially cured, sealing said metal thin wires and said semiconductor chip with more of said encapsulating.

Please add the following claims:

8. The semiconductor device as claimed in claim 1, wherein said adhesive layer covers the entire principle surface of said heat spreader.

9. The method as claimed in claim 5, wherein said connecting electrodes is performed after said sealing said second adhesive layer and part of said semiconductor chip with a first encapsulating resin, and before said sealing said metal thin wires and said semiconductor chip with a second encapsulating resin.